

Attorney Docket No. 5308-413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.
Application No.: 10/849,617
Filed: May 20, 2004
For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS

U.S. Patent No.: 7,432,142 B2
Issued: October 7, 2008
Confirmation No: 9882

October 28, 2008

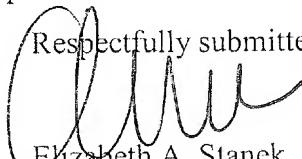
Commissioner for Patents
Attn: Certificate of Correction Branch
P.O. Box 1450
Alexandria, VA 22313-1450

**REQUEST FOR ENTRY OF CERTIFICATE OF CORRECTION UNDER
No. 35 U.S.C §254 AND 37 C.F.R. §1.322**

Sir:

The Assignee of record for the above-referenced patent hereby requests, pursuant to 35 U.S.C §254 and 37 C.F.R. §1.322, that a Certificate of Correction be issued. This request is made in order to correct the mistakes incurred through the fault of the U.S. Patent and Trademark Office. The mistakes appearing in the patent are set forth with corrections on the Certificate of Correction enclosed herewith. The Assignee further directs the Commissioner's attention to the attached IDS considered on 04/05/2006.

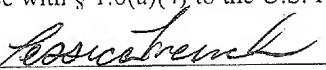
No fee is believed due. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

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CERTIFICATION OF ELECTRONIC TRANSMISSION

I hereby certify that this correspondence is being transmitted via the Office electronic filing system in accordance with § 1.6(a)(4) to the U.S. Patent and Trademark Office on October 28, 2008.



Jessica M. French

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page 1 of 1

PATENT NO. : 7,432,142 B2

APPLICATION NO.: 10/849,617

DATED : October 7, 2008

INVENTOR(S) : Saxler et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Item 56, References Cited, Foreign Patent Documents, Page 2:

Please correct "JP 2001230401 A 8/2001"

To read -- JP 2001230407 A 8/2001 --

In the Claims:

Column 14, Claim 5, Line 40: Please correct "baffler"

To read -- barrier --

Column 14, Claim 5, Line 46: Please correct "baffler"

To read -- barrier --

Column 15, Claim 16, Line 52: Please correct "baffler"

To read -- barrier --

MAILING ADDRESS OF SENDER:

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	A2	of	A3	Date if Known
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Attorney Docket Number	5308-392
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
KBD	44.	PCT	WO 03/049193	A1	Cree, Inc.	06-12-2003	
	45.	JP	2002016087	A	NEC Corp	01-18-2002	Abstract
	46.	JP	2001230407	A	Matsushita Electric Industrial Co. Ltd.	08-24-2001	Abstract
	47.	PCT	WO 01/57929	A1	Oree Lighting Company	08-09-2001	
	48.	JP	10-050982		Nippon Telegraph & Telephone Corp.	02-20-1998	Abstract
	49.	PCT	WO 93/23877	A1	Massachusetts Institute of Technology	11-25-1993	
	50.	EP	0 563 847	A2	Matsushita Electric Industrial Co., Ltd.	10-06-1993	

OTHER NON PATENT LITERATURE DOCUMENTS							
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published					T
KBD	51.	Asbeck et al. "Piezoelectric charge densities in AlGaN/GaN HFETs," <i>Electronics Letters</i> . Vol. 33, No. 14, pp. 1230-1231 (1997).					
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	62.	Gelmont et al. "Monte Carlo simulation of electron transport in gallium nitride," <i>Journal of Applied Physics</i> . Vol. 74, No. 3, pp. 1818-1821 (August 1993).					
	63.	Heikman, et al., "Mass Transport Regrowth of GaN for Ohmic Contacts to AlGaN/GaN," <i>Applied Physics Letters</i> . Vol. 78, No. 19, pp. 2876					
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Examiner Signature	<i>John F. Dunn</i>	Date Considered	4/15/2006
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.